## MC74HC4060A

## 14-Stage Binary Ripple Counter With Oscillator

## High-Performance Silicon-Gate CMOS

The MC74HC4060A is identical in pinout to the standard CMOS MC14060B. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of 14 master-slave flip-flops and an oscillator with a frequency that is controlled either by a crystal or by an RC circuit connected externally. The output of each flip-flop feeds the next and the frequency at each output is half of that of the preceding one. The state of the counter advances on the negative-going edge of the Osc In. The active-high Reset is asynchronous and disables the oscillator to allow very low power consumption during stand-by operation.

State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and may have to be gated with Osc Out 2 of the HC4060A.

## Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: $1 \mu \mathrm{~A}$
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With JEDEC Standard No. 7A Requirements
- Chip Complexity: 390 FETs or 97.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant


ON Semiconductor ${ }^{\circledR}$
www.onsemi.com


MARKING DIAGRAMS



TSSOP-16
A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G or • = Pb-Free Package
(Note: Microdot may be in either location)
FUNCTION TABLE

| Clock | Reset | Output State |
| :---: | :---: | :---: |
| $\sim$ | L | No Change |
| $\sim$ | L | Advance to Next State |
| X | H | All Outputs Are Low |

ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\text {in }}$ | DC Input Voltage (Referenced to GND) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{~V}_{\text {out }}$ | DC Output Voltage (Referenced to GND) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{I}_{\text {in }}$ | DC Input Current, per Pin | $\pm 20$ | mA |
| $\mathrm{I}_{\text {out }}$ | DC Output Current, per Pin | $\pm 25$ | mA |
| $\mathrm{I}_{\mathrm{CC}}$ | DC Supply Current, $\mathrm{V}_{\mathrm{CC}}$ and GND Pins | $\pm 50$ | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation in Still Air,SOIC Packaget <br> TSSOP Packaget | 500 | mW |
|  |  | 450 |  |
| $\mathrm{~T}_{\text {stg }}$ | Storage Temperature Range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 Seconds |  |  |
|  | SOIC or TSSOP Package |  |  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
$\dagger$ Derating: SOIC Package: $-7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$
TSSOP Package: $-6.1 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | $2.5^{*}$ | 6.0 | V |
| $\mathrm{~V}_{\text {in }}, \mathrm{V}_{\text {out }}$ | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | $\mathrm{~V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range, All Package Types |  | -55 | +125 |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise/Fall Time | ${ }^{\circ} \mathrm{C}$ |  |  |
|  | (Figure 1) | $\mathrm{V}_{\mathrm{CC}}=2.0 \mathrm{~V}$ | 0 | 1000 |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=4.5 \mathrm{~V}$ | 0 | ns |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=6.0 \mathrm{~V}$ | 0 | 500 |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.
*The oscillator is guaranteed to function at 2.5 V minimum. However, parametrics are tested at 2.0 V by driving Pin 11 with an external clock source.

DC CHARACTERISTICS (Voltages Referenced to GND)


DC CHARACTERISTICS (Voltages Referenced to GND) (continued)

| Symbol | Parameter | Condition |  | $\underset{\mathrm{V}}{\mathrm{v}_{\mathrm{cc}}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | -55 to $25^{\circ} \mathrm{C}$ | $\leq 85{ }^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{OH}}$ | Minimum High-Level Output Voltage (Osc Out 1, Osc Out 2) | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{CC}} \text { or GND } \\ & \mathrm{I}_{\text {out }} \leq 20 \mu \mathrm{~A} \end{aligned}$ |  |  | $\begin{aligned} & 2.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | V |
|  |  | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\text {cc }}$ or GND | $\begin{aligned} & \left\|\left.\right\|_{\text {out }} \leq 0.7 \mathrm{~mA}\right. \\ & \left\|\left.\right\|_{\text {out }}\right\| \leq 1.0 \mathrm{~mA} \\ & \left\|\left.\right\|_{\text {out }}\right\| \leq 1.3 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 2.48 \\ & 3.98 \\ & 5.48 \end{aligned}$ | $\begin{aligned} & 2.34 \\ & 3.84 \\ & 5.34 \end{aligned}$ | $\begin{aligned} & 2.20 \\ & 3.70 \\ & 5.20 \end{aligned}$ |  |  |
| $\mathrm{V}_{\text {OL }}$ | Maximum Low-Level Output Voltage (Osc Out 1, Osc Out 2) | $\begin{aligned} & \begin{array}{l} \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{CC}} \text { or GND } \\ \mid \\|_{\text {out }} \leq 20 \mu \mathrm{~A} \end{array} \end{aligned}$ |  | $\begin{aligned} & \hline 2.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | V |  |
|  |  | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\text {CC }}$ or GND | $\mid{ }_{\text {out }} \leq 0.7 \mathrm{~mA}$ <br> $\mid l_{\text {out }} \leq 1.0 \mathrm{~mA}$ <br> $\left\|{ }_{\text {out }}\right\| \leq 1.3 \mathrm{~mA}$ | $\begin{aligned} & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 0.26 \\ & 0.26 \\ & 0.26 \end{aligned}$ | $\begin{aligned} & 0.33 \\ & 0.33 \\ & 0.33 \end{aligned}$ | $\begin{aligned} & 0.40 \\ & 0.40 \\ & 0.40 \end{aligned}$ |  |  |
| $\mathrm{l}_{\text {in }}$ | Maximum Input Leakage Current | $V_{\text {in }}=V_{\text {cc }}$ or GND |  | 6.0 | $\pm 0.1$ | $\pm 1.0$ | $\pm 1.0$ | $\mu \mathrm{A}$ |  |
| Icc | Maximum Quiescent Supply Current (per Package) | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{CC}} \text { or GND } \\ & \mathrm{I}_{\text {out }}=0 \mu \mathrm{~A} \end{aligned}$ |  | 6.0 | 4 | 40 | 160 | $\mu \mathrm{A}$ |  |

AC CHARACTERISTICS $\left(\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}\right.$, Input $\left.\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=6 \mathrm{~ns}\right)$

| Symbol | Parameter | $\underset{\mathrm{V}}{\mathrm{v}_{\mathrm{cc}}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | -55 to $25^{\circ} \mathrm{C}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{f}_{\text {max }}$ | Maximum Clock Frequency (50\% Duty Cycle) (Figures 1 and 4) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & \hline 6.0 \\ & 10 \\ & 30 \\ & 50 \end{aligned}$ | $\begin{aligned} & \hline 9.0 \\ & 14 \\ & 28 \\ & 45 \end{aligned}$ | $\begin{aligned} & 8.0 \\ & 12 \\ & 25 \\ & 40 \end{aligned}$ | MHz |
| $\begin{aligned} & \text { tpLH, } \\ & t_{\text {PHL }} \end{aligned}$ | Maximum Propagation Delay, Osc In to Q4* (Figures 1 and 4) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 300 \\ & 180 \\ & 60 \\ & 51 \end{aligned}$ | $\begin{gathered} 375 \\ 200 \\ 75 \\ 64 \end{gathered}$ | $\begin{gathered} 450 \\ 250 \\ 90 \\ 75 \end{gathered}$ | ns |
| $t_{\text {pLH }}$, <br> $\mathrm{t}_{\mathrm{PHL}}$ | Maximum Propagation Delay, Osc In to Q14* (Figures 1 and 4) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 500 \\ & 350 \\ & 250 \\ & 200 \end{aligned}$ | $\begin{aligned} & 750 \\ & 450 \\ & 275 \\ & 220 \end{aligned}$ | $\begin{gathered} 1000 \\ 600 \\ 300 \\ 250 \end{gathered}$ | ns |
| $\mathrm{t}_{\text {PHL }}$ | Maximum Propagation Delay, Reset to Any Q (Figures 2 and 4) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 195 \\ & 75 \\ & 39 \\ & 33 \end{aligned}$ | $\begin{gathered} 245 \\ 100 \\ 49 \\ 42 \end{gathered}$ | $\begin{gathered} 300 \\ 125 \\ 61 \\ 53 \end{gathered}$ | ns |
| $\begin{aligned} & \hline \mathrm{t}_{\mathrm{PLH}}, \\ & \mathrm{t}_{\mathrm{PH}} \end{aligned}$ | Maximum Propagation Delay, Qn to Qn+1 (Figures 3 and 4) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & \hline 75 \\ & 60 \\ & 15 \\ & 13 \\ & \hline \end{aligned}$ | $\begin{aligned} & 95 \\ & 75 \\ & 19 \\ & 16 \end{aligned}$ | $\begin{gathered} 125 \\ 95 \\ 24 \\ 20 \end{gathered}$ | ns |

AC CHARACTERISTICS $\left(C_{L}=50 \mathrm{pF}\right.$, Input $\left.\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=6 \mathrm{~ns}\right)$ - continued

| Symbol | Parameter | $\stackrel{\mathrm{v}_{\mathrm{Cc}}}{\mathbf{V}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | -55 to $25^{\circ} \mathrm{C}$ | $\leq 85{ }^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| ${ }_{\text {t }}^{\text {tLH }}$, | Maximum Output Transition Time, Any Output | 2.0 | 75 | 95 | 110 | ns |
| $\mathrm{t}_{\text {thL }}$ | (Figures 1 and 4) | 3.0 | 27 | 32 | 36 |  |
|  |  | 4.5 | 15 | 19 | 22 |  |
|  |  | 6.0 | 13 | 16 | 19 |  |
| $\mathrm{C}_{\text {in }}$ | Maximum Input Capacitance |  | 10 | 10 | 10 | pF |

* For $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ and $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$, typical propagation delay from Clock to other Q outputs may be calculated with the following equations:
$\mathrm{V}_{\mathrm{CC}}=2.0 \mathrm{~V}: \mathrm{t}_{\mathrm{p}}=[93.7+59.3(\mathrm{n}-1)] \mathrm{ns}$
$\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}: \mathrm{t}_{\mathrm{p}}=[61.5+34.4(\mathrm{n}-1)] \mathrm{ns}$
$\mathrm{V}_{\mathrm{CC}}=4.5 \mathrm{~V}: \mathrm{tp}_{\mathrm{p}}=[30.25+14.6(\mathrm{n}-1)] \mathrm{ns}$
$\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}: \mathrm{t}_{\mathrm{P}}=[61.5+34.4(\mathrm{n}-1)] \mathrm{ns}$
$\mathrm{V}_{\mathrm{CC}}=6.0 \mathrm{~V}: \mathrm{tp}_{\mathrm{p}}=[24.4+12(\mathrm{n}-1)] \mathrm{ns}$

| CPD |  | Typical @ $25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$ | pF |
| :---: | :---: | :---: | :---: |
|  | Power Dissipation Capacitance (Per Package)* | 35 |  |

*Used to determine the no-load dynamic power consumption: $\mathrm{P}_{\mathrm{D}}=\mathrm{C}_{\mathrm{PD}} \mathrm{V}_{\mathrm{CC}}{ }^{2 \mathrm{f}}+\mathrm{I}_{\mathrm{CC}} \mathrm{V}_{\mathrm{CC}}$.

TIMING REQUIREMENTS (Input $t_{r}=t_{f}=6 \mathrm{~ns}$ )

|  | Parameter | $\underset{\mathrm{V}}{\mathrm{v}_{\mathrm{cc}}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Symbol |  |  | -55 to $25^{\circ} \mathrm{C}$ | $\leq 85{ }^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{t}_{\text {rec }}$ | Minimum Recovery Time, Reset Inactive to Clock (Figure 2) | 2.0 | 100 | 125 | 150 | ns |
|  |  | 3.0 | 75 | 100 | 120 |  |
|  |  | 4.5 | 20 | 25 | 30 |  |
|  |  | 6.0 | 17 | 21 | 25 |  |
| $\mathrm{t}_{\text {w }}$ | Minimum Pulse Width, Clock (Figure 1) | 2.0 | 75 | 95 | 110 | ns |
|  |  | 3.0 | 27 | 32 | 36 |  |
|  |  | 4.5 | 15 | 19 | 23 |  |
|  |  | 6.0 | 13 | 16 | 19 |  |
| $\mathrm{t}_{\text {w }}$ | Minimum Pulse Width, Reset (Figure 2) | 2.0 | 75 | 95 | 110 | ns |
|  |  | 3.0 | 27 | 32 | 36 |  |
|  |  | 4.5 | 15 | 19 | 23 |  |
|  |  | 6.0 | 13 | 16 | 19 |  |
| $\mathrm{tr}_{\mathrm{r}} \mathrm{t}_{\mathrm{f}}$ | Maximum Input Rise and Fall Times (Figure 1) | 2.0 | 1000 | 1000 | 1000 | ns |
|  |  | 3.0 | 800 | 800 | 800 |  |
|  |  | 4.5 | 500 | 500 | 500 |  |
|  |  | 6.0 | 400 | 400 | 400 |  |

## ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :--- | :---: |
| MC74HC4060ADG | SOIC-16 <br> (Pb-Free) | 48 Units / Rail |
| MC74HC4060ADR2G | SOIC-16 <br> (Pb-Free) | 2500 Units / Reel |
| NLV74HC4060ADR2G* | SOIC-16 <br> (Pb-Free) | 2500 Units / Reel |
| MC74HC4060ADTG | TSSOP-16 <br> (Pb-Free) | 96 Units / Rail |
| MC74HC4060ADTR2G | TSSOP-16 <br> (Pb-Free) | 2500 Units / Reel |
| NLVHC4060ADTR2G* | TSSOP-16 <br> (Pb-Free) | 2500 Units / Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

## MC74HC4060A

## PIN DESCRIPTIONS

## INPUTS

## Osc In (Pin 11)

Negative-edge triggering clock input. A high-to-low transition on this input advances the state of the counter. Osc In may be driven by an external clock source.

## Reset (Pin 12)

Active-high reset. A high level applied to this input asynchronously resets the counter to its zero state (forcing all Q outputs low) and disables the oscillator.

## OUTPUTS

Q4-Q10, Q12-Q14 (Pins 7, 5, 4, 6, 13, 15, 1, 2, 3)
Active-high outputs. Each Qn output divides the Clock input frequency by $2^{\mathrm{N}}$. The user should note the Q1, Q2, Q3 and Q11 are not available as outputs.

## Osc Out 1, Osc Out 2 (Pins 9, 10)

Oscillator outputs. These pins are used in conjunction with Osc In and the external components to form an oscillator. When Osc In is being driven with an external clock source, Osc Out 1 and Osc Out 2 must be left open circuited. With the crystal oscillator configuration in Figure 6, Osc Out 2 must be left open circuited.


Figure 1.


Figure 3.


Figure 2.

*Includes all probe and jig capacitance
Figure 4. Test Circuit


Figure 5. Expanded Logic Diagram


$$
\begin{aligned}
& \text { For } 2.0 \mathrm{~V} \leq \mathrm{V}_{\mathrm{Cc}} \leq 6.0 \mathrm{~V} \\
& \\
& \quad 10 \mathrm{R}_{\mathrm{tc}}>\mathrm{R}_{\mathrm{S}}>2 R_{\mathrm{tc}} \\
& \quad 400 \mathrm{~Hz} \leq \mathrm{f} \leq 400 \mathrm{Khz} \text { : } \\
& \mathrm{f} \approx \frac{1}{2.2 \mathrm{R}_{\mathrm{tc}} \mathrm{C}_{\mathrm{tc}}} \text { (f in Hz, } \mathrm{R}_{\mathrm{tc}} \text { in ohms, } \mathrm{C}_{\mathrm{tc}} \text { in farads) } \\
& \text { The formula may vary for other frequencies. }
\end{aligned}
$$

Figure 6. Oscillator Circuit Using RC Configuration


Figure 7. Pierce Crystal Oscillator Circuit

TABLE 1. CRYSTAL OSCILLATOR AMPLIFIER SPECIFICATIONS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$; Input $=$ Pin 11 , Output $\left.=\operatorname{Pin} 10\right)$

| Type |  | Positive Reactance (Pierce) |
| :---: | :---: | :---: |
| Input Resistance, $\mathrm{R}_{\text {in }}$ |  | 60M $\Omega$ Minimum |
| Output Impedance, $\mathrm{Z}_{\text {out }}$ (4.5V Supply) |  | $200 \Omega$ (See Text) |
| Input Capacitance, $\mathrm{C}_{\text {in }}$ |  | 5pF Typical |
| Output Capacitance, $\mathrm{C}_{\text {out }}$ |  | 7pF Typical |
| Series Capacitance, $\mathrm{C}_{\mathrm{a}}$ |  | 5pF Typical |
| Open Loop Voltage Gain with Output at Full Swing, $\alpha$ | 3Vdc Supply 4Vdc Supply 5Vdc Supply 6Vdc Supply | 5.0 Expected Minimum <br> 4.0 Expected Minimum <br> 3.3 Expected Minimum <br> 3.1 Expected Minimum |

## PIERCE CRYSTAL OSCILLATOR DESIGN



Value are supplied by crystal manufacturer (parallel resonant crystal).
Figure 8. Equivalent Crystal Networks


NOTE: $\mathrm{C}=\mathrm{C} 1+\mathrm{C}_{\text {in }}$ and $\mathrm{R}=\mathrm{R} 1+\mathrm{R}_{\text {out }} \cdot \mathrm{C}_{0}$ is considered as part of the load. $C_{a}$ and $R_{f}$ typically have minimal effect below 2 MHz .

Figure 9. Series Equivalent Crystal Load


Values are listed in Table 1.

Figure 10. Parasitic Capacitances of the Amplifier

## MC74HC4060A

## DESIGN PROCEDURES

The following procedure applies for oscillators operating below 2 MHz where Z is a resistor R 1 . Above 2 MHz , additional impedance elements should be considered: $C_{\text {out }}$ and $C_{a}$ of the amp, feedback resistor $R_{f}$, and amplifier phase shift error from $180^{\circ} \mathrm{C}$.

Step 1: Calculate the equivalent series circuit of the crystal at the frequency of oscillation.

$$
Z_{e}=\frac{-j X_{C_{0}}\left(R_{S}+j X_{L_{s}}-j X_{C_{S}}\right)}{-j X_{C_{0}}+R_{S}+j X_{L_{s}}-j X_{C_{S}}}=R_{e}+j X_{e}
$$

Reactance $\mathrm{j} \mathrm{X}_{\mathrm{e}}$ should be positive, indicating that the crystal is operating as an inductive reactance at the oscillation frequency. The maximum $R_{s}$ for the crystal should be used in the equation.

Step 2: Determine $\beta$, the attenuation, of the feedback network. For a closed-loop gain of $2, A_{\nu} \beta=2, \beta=2 / A_{\nu}$ where $A_{\nu}$ is the gain of the HC4060A amplifier.

Step 3: Determine the manufacturer's loading capacitance. For example: A manufacturer may specify an external load capacitance of 32 pF at the required frequency.

Step 4: Determine the required Q of the system, and calculate $\mathrm{R}_{\text {load }}$, For example, a manufacturer specifies a crystal Q of 100,000 . In-circuit $Q$ is arbitrarily set at $20 \%$ below crystal $Q$ or 80,000 . Then $R_{\text {load }}=\left(2 \pi f_{0} L_{S} / Q\right)-R_{s}$ where $L_{s}$ and $R_{s}$ are crystal parameters.

Step 5: Simultaneously solve, using a computer,

$$
\begin{align*}
& \left.\beta=\frac{X_{C} \cdot X_{C 2}}{R \cdot R_{e}+X_{C 2}\left(X_{e}-X_{C}\right)} \text { (with feedback phase shift }=180^{\circ}\right) \\
& X_{e}=X_{C 2}+X_{C}+\frac{R_{e} X_{C 2}}{R}=X_{C l o a d} \quad\left(\text { where the loading capacitor is an external load, not including } C_{0}\right) \\
& R_{\text {load }}=\frac{R X_{C_{0}} X_{C 2}\left[\left(X_{C}+X_{C 2}\right)\left(X_{C}+X_{C}\right)-X_{C}\left(X_{C}+X_{C}+X_{C 2}\right)\right]}{X_{C 2}{ }_{C 2}\left(X_{C}+X_{C_{0}}\right)^{2}+R^{2}\left(X_{C}+X_{C_{0}}+X_{C 2}\right)^{2}}
\end{align*}
$$

( Eq 3

Here $R=R_{\text {out }}+R 1$. $R_{\text {out }}$ is amp output resistance, $R 1$ is $Z$. The $C$ corresponding to $X_{C}$ is given by $C=C 1+C_{i n}$.
Alternately, pick a value for R 1 (i.e, let $\mathrm{R} 1=\mathrm{R}_{\mathrm{S}}$ ). Solve Equations 1 and 2 for C 1 and C 2 . Use Equation 3 and the fact that $\mathrm{Q}=2 \pi \mathrm{f}_{\mathrm{o}} \mathrm{L}_{\mathrm{S}} /\left(\mathrm{R}_{\mathrm{S}}+\mathrm{R}_{\text {load }}\right)$ to find in-circuit Q . If Q is not satisfactory pick another value for R 1 and repeat the procedure.

CHOOSING R1
Power is dissipated in the effective series resistance of the crystal. The drive level specified by the crystal manufacturer is the maximum stress that a crystal can withstand without damage or excessive shift in frequency. R1 limits the drive level.

To verify that the maximum dc supply voltage does not overdrive the crystal, monitor the output frequency as a function of voltage at Osc Out 2 (Pin 9). The frequency should increase very slightly as the dc supply voltage is increased. An overdriven crystal will decrease in frequency or become unstable with an increase in supply voltage. The operating supply voltage must be reduced or R1 must be increased in value if the overdriven condition exists. The user should note that the oscillator start-up time is proportional to the value of R1.

## SELECTING $\mathbf{R}_{\mathbf{f}}$

The feedback resistor, $\mathrm{R}_{\mathrm{f}}$, typically ranges up to $20 \mathrm{M} \Omega$. $\mathrm{R}_{\mathrm{f}}$ determines the gain and bandwidth of the amplifier. Proper bandwidth insures oscillation at the correct frequency plus roll-off to minimize gain at undesirable frequencies, such as
the first overtone. $\mathrm{R}_{\mathrm{f}}$ must be large enough so as to not affect the phase of the feedback network in an appreciable manner.

## ACKNOWLEDGEMENTS AND RECOMMENDED REFERENCES

The following publications were used in preparing this data sheet and are hereby acknowledged and recommended for reading:
Technical Note TN-24, Statek Corp.
Technical Note TN-7, Statek Corp.
D. Babin, "Designing Crystal Oscillators", Machine Design, March 7, 1985.
D. Babin, "Guidelines for Crystal Oscillator Design", Machine Design, April 25, 1985.

## ALSO RECOMMENDED FOR READING:

E. Hafner, "The Piezoelectric Crystal Unit-Definitions and Method of Measurement", Proc. IEEE, Vol. 57, No. 2, Feb., 1969.
D. Kemper, L. Rosine, "Quartz Crystals for Frequency Control", Electro-Technology, June, 1969.
P. J. Ottowitz, "A Guide to Crystal Selection", Electronic Design, May, 1966.


Figure 11. Timing Diagram

SOIC-16 9.90x3.90×1.50 1.27P
CASE 751B
ISSUE L
DATE 29 MAY 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.


| MILLIMETERS |  |  |  |
| :---: | :---: | :---: | :---: |
| DIM | MIN | NOM | MAX |
| A | 1.35 | 1.55 | 1.75 |
| A1 | 0.00 | 0.05 | 0.10 |
| A2 | 1.35 | 1.50 | 1.65 |
| b | 0.35 | 0.42 | 0.49 |
| c | 0.19 | 0.22 | 0.25 |
| D | 9.90 BSC |  |  |
| E | 6.00 BSC |  |  |
| E1 | 3.90 BSC |  |  |
| e | 1.27 BSC |  |  |
| h | 0.25 | --- | 0.50 |
| L | 0.40 | 0.83 | 1.25 |
| L1 | 1.05 REF |  |  |
| O | 0 | --- | $7 \cdot$ |
| TOLERANCE OF FORM AND POSITION |  |  |  |
| aaa | 0.10 |  |  |
| bbb | 0.20 |  |  |
| ccc | 0.10 |  |  |
| ddd | 0.25 |  |  |
| eee | 0.10 |  |  |



RECOMMENDED MOUNTING FOOTPRINT
*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

| DOCUMENT NUMBER: | 98ASB42566B |  | Document Repositon: rin red. |
| :---: | :---: | :---: | :---: |
| DESCRIPTION: | SOIC-16 9.90X3.90X1.50 1.27P |  | PAGE 1 OF 2 |

[^0] special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

## SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

## GENERIC

MARKING DIAGRAM*

*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1: |  | STYLE 2: |  | STYLE 3: |  | STYLE 4: |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| PIN 1. | COLLECTOR | PIN 1. | CATHODE | PIN 1. | COLLECTOR, DYE \#1 | PIN 1. | COLLECTOR, DYE \#1 |
| 2. | BASE | 2. | ANODE | 2. | BASE, \#1 | 2. | COLLECTOR, \#1 |
| 3. | Emitter | 3. | NO CONNECTION | 3. | EMITTER, \#1 | 3. | COLLECTOR, \#2 |
| 4. | NO CONNECTION | 4. | CATHODE | 4. | COLLECTOR, \#1 | 4. | COLLECTOR, \#2 |
| 5. | EMITTER | 5. | CATHODE | 5. | COLLECTOR, \#2 | 5. | COLLECTOR, \#3 |
| 6. | BASE | 6. | NO CONNECTION | 6. | BASE, \#2 | 6. | COLLECTOR, \#3 |
| 7. | COLLECTOR | 7. | ANODE | 7. | EMITTER, \#2 | 7. | COLLECTOR, \#4 |
| 8. | COLLECTOR | 8. | CATHODE | 8. | COLLECTOR, \#2 | 8. | COLLECTOR, \#4 |
| 9. | BASE | 9. | CATHODE | 9. | COLLECTOR, \#3 | 9. | BASE, \#4 |
| 10. | EMITTER | 10. | ANODE | 10. | BASE, \#3 | 10. | EMITTER, \#4 |
| 11. | NO CONNECTION | 11. | NO CONNECTION | 11. | EMITTER, \#3 | 11. | BASE, \#3 |
| 12. | EMITTER | 12. | CATHODE | 12. | COLLECTOR, \#3 | 12. | EMITTER, \#3 |
| 13. | BASE | 13. | CATHODE | 13. | COLLECTOR, \#4 | 13. | BASE, \#2 |
| 14. | COLLECTOR | 14. | NO CONNECTION | 14. | BASE, \#4 | 14. | EMITTER, \#2 |
| 15. | EMITTER | 15. | ANODE | 15. | EMITTER, \#4 | 15. | BASE, \#1 |
| 16. | COLLECTOR | 16. | CATHODE | 16. | COLLECTOR, \#4 | 16. | EMITTER, \#1 |
| STYLE 5: |  | STYLE 6: |  | STYLE 7: |  |  |  |
| PIN 1. | DRAIN, DYE \#1 | PIN 1. | CATHODE | PIN 1. | SOURCE N-CH |  |  |
| 2. | DRAIN, \#1 | 2. | CATHODE | 2. | COMMON DRAIN (OUTPUT) |  |  |
| 3. | DRAIN, \#2 | 3. | CATHODE | 3. | COMMON DRAIN (OUTPUT) |  |  |
| 4. | DRAIN, \#2 | 4. | CATHODE | 4. | GATE P-CH |  |  |
| 5. | DRAIN, \#3 | 5. | CATHODE | 5. | COMMON DRAIN (OUTPUT) |  |  |
| 6. | DRAIN, \#3 | 6. | CATHODE | 6. | COMMON DRAIN (OUTPUT) |  |  |
| 7. | DRAIN, \#4 | 7. | CATHODE | 7. | COMMON DRAIN (OUTPUT) |  |  |
| 8. | DRAIN, \#4 | 8. | CATHODE | 8. | SOURCE P-CH |  |  |
| 9. | GATE, \#4 | 9. | ANODE | 9. | SOURCE P-CH |  |  |
| 10. | SOURCE, \#4 | 10. | ANODE | 10. | COMMON DRAIN (OUTPUT) |  |  |
| 11. | GATE, \#3 | 11. | ANODE | 11. | COMMON DRAIN (OUTPUT) |  |  |
| 12. | SOURCE, \#3 | 12. | ANODE | 12. | COMMON DRAIN (OUTPUT) |  |  |
| 13. | GATE, \#2 | 13. | ANODE | 13. | GATE N-CH |  |  |
| 14. | SOURCE, \#2 | 14. | ANODE | 14. | COMMON DRAIN (OUTPUT) |  |  |
| 15. | GATE, \#1 | 15. | ANODE | 15. | COMMON DRAIN (OUTPUT) |  |  |
| 16. | SOURCE, \#1 | 16. | ANODE | 16. | SOURCE N-CH |  |  |


| DOCUMENT NUMBER: | 98ASB42566B | Electronic Versions are uncontrolled except when accessed directly from the Document Repository. <br> Printed versions are uncontroled except when stamped "CONTROLLED COPY" in red. |
| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SOIC-16 9.90X3.90X1.501.27P | PAGE 2 OF 2 |

[^1]

TSSOP-16 WB
CASE 948F
ISSUE B
DATE 19 OCT 2006


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 ( 0.006 ) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 ( 0.010 ) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL in EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE - $W$ -

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 4.90 | 5.10 | 0.193 | 0.200 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| c |  | 1.20 |  | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | SC | 0.026 | BSC |
| H | 0.18 | 0.28 | 0.007 | 0.011 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BC | 0.25 | BSC |
| M | $0^{\circ}$ | $8^{\circ}$ | $0^{\circ}$ | $8^{\circ}$ |



| GENERIC <br> MARKING DIAGRAM* |  |
| :---: | :---: |
|  |  |
| XXXX | = Specific Device Code |
| A | = Assembly Location |
| L | = Wafer Lot |
| Y | = Year |
| W | = Work Week |
| G or - | = Pb-Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " $\mathrm{\bullet}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| DOCUMENT NUMBER: | 98ASH70247A | Electronic versions are uncontrolled except when accessed directly from the Document Repository. <br> Printed versions are uncontroled except when stamped "CONTROLLED COPY" in red. |
| ---: | :--- | :--- | :--- |
| DESCRIPTION: | TSSOP-16 | PAGE 1 OF 1 |

[^2]onsemi, OnSeMi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner

## ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales


[^0]:    onsemi and OnSemi. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation

[^1]:    onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

[^2]:    onsemi and OnSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

